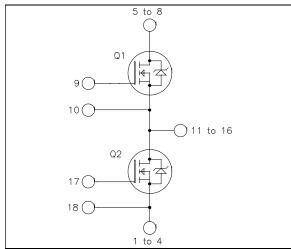
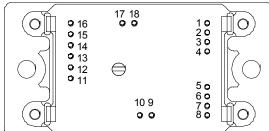


Phase leg Super Junction MOSFET Power Module

$$\begin{split} V_{DSS} &= 900V \\ R_{DSon} &= 60 m\Omega \ max \ @ \ Tj = 25^{\circ}C \\ I_D &= 59A \ @ \ Tc = 25^{\circ}C \end{split}$$





Pins 1/2/3/4 ; 5/6/7/8 ; 11/12/13/14/15/16 must be shorted together

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- CoolMOSTM
 - Ultra low R_{DSon}
 - Low Miller capacitance
 - Ultra low gate charge
 - Avalanche energy rated
 - Very rugged
 - Very low stray inductance
- Kelvin source for easy drive
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

All ratings @ $T_i = 25^{\circ}C$ unless otherwise specified

Absolute maximum ratings

ADSUIUL	e maximum ratings			
Symbol	Parameter		Max ratings	Unit
$V_{ m DSS}$	Drain - Source Breakdown Voltage		900	V
Ţ	Continuous Drain Current	$T_c = 25$ °C	59	
I_D		$T_c = 80$ °C	44	Α
I_{DM}	Pulsed Drain current		150	
V_{GS}	Gate - Source Voltage		±20	V
R_{DSon}	Drain - Source ON Resistance		60	mΩ
P_{D}	Maximum Power Dissipation	$T_c = 25$ °C	462	W
I_{AR}	Avalanche current (repetitive and non repetitive)		8.8	A
E_{AR}	Repetitive Avalanche Energy		2.9	mJ
E _{AS}	Single Pulse Avalanche Energy		1940	1113

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 900V$			200	μΑ
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 52A$		50	60	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 6mA$	2.5	3	3.5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			200	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V ; V_{DS} = 100V$ f = 1MHz			13.6		nF
C_{oss}	Output Capacitance				0.66		
Q_{g}	Total gate Charge	$\begin{aligned} &V_{GS} = 10V \\ &V_{Bus} = 400V \\ &I_D = 52A \end{aligned}$			540		nC
Q_{gs}	Gate – Source Charge				64		
Q_{gd}	Gate – Drain Charge				230		
$T_{d(on)}$	Turn-on Delay Time	$ \begin{array}{c} \textbf{Inductive Switching (125°C)} \\ V_{GS} = 10V \\ V_{Bus} = 600V \\ I_D = 52A \\ R_G = 3.8\Omega \end{array} $			70		ns
T_{r}	Rise Time				20		
$T_{d(off)}$	Turn-off Delay Time				400		
T_{f}	Fall Time				25		
Е	Turn-off Switching Energy	Inductive switching V _{GS} =10V; I _D =52A	$T_j = 25$ °C		1.5		mJ
E_{off}		1 95 / 5	$T_j = 125$ °C		1.7		1113
R_{thJC}	Junction to Case Thermal Resistance	2				0.27	°C/W

Source - Drain diode ratings and characteristics

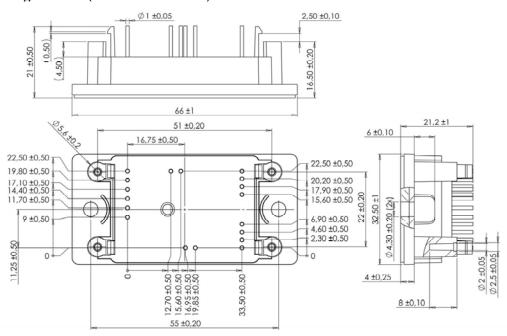
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_S	Continuous Source current		Tc = 25°C			59	Α
	(Body diode)		$Tc = 80^{\circ}C$			44	
V_{SD}	Diode Forward Voltage	$V_{GS} = 0V, I_S = -52A$			0.8	1.2	V
t_{rr}	Reverse Recovery Time	$I_S = -52A$	$T_j = 25^{\circ}C$		920		ns
Q _{rr}	Reverse Recovery Charge	$V_R = 400V$ $di_S/dt = 200A/\mu s$	$T_j = 25^{\circ}C$		60		μС

Thermal and package characteristics

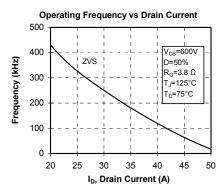
Symbol	Characteristic			Min	Тур	Max	Unit
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range			-40		150	
T_{STG}	Storage Temperature Range			-40		125	°C
T_{C}	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight		•			75	g

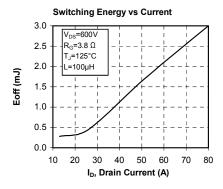


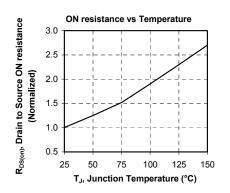
SP2 Package outline (dimensions in mm)

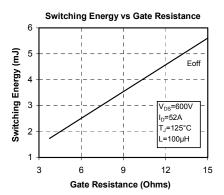


Typical CoolMOS Performance Curve



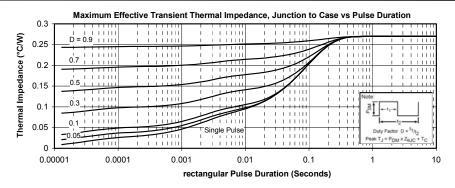


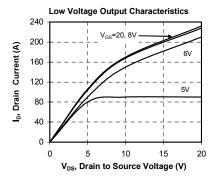


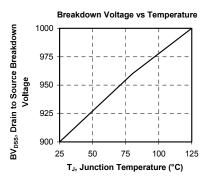


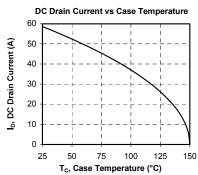
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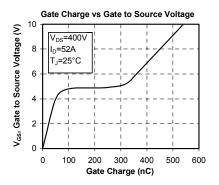


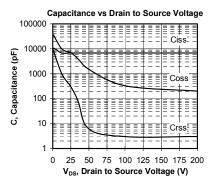












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